Total No. of Questions: 12]	SEAT No.:

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[4859]-219

B.E. (Computer) (Semester- II) VLSIAND DIGITAL SYSTEM DESIGN (2008 Pattern) (Elective-IV) Time: 3 Hours] [Maximum Marks: 100] Instructions to the candidates: Answers to the two sections should be written in separate answer books. Neat diagrams must be drawn wherever necessary. 2) Figures to the right indicate full marks. 3) Assume suitable data if necessary. 4) **SECTION-I** Explain design methodology with flow chart for ASIC design. **Q1**) a) [8] Explain the role of technology scaling in growth of IC Design. b) [9] OR *Q2*) a) Explain the need of layout design rules. Explain design rules for interconnects. [9] Explain the classification of IC technology based on circuit technology. [8] b) Explain Shallow Trench Isolation (STI) with process flow. **Q3)** a) [8] Explain limitations of further scaling of CMOS device. b) [9] OR Explain geometry parameters of interconnects. Explain merits and *Q4*) a) demerits of Cu interconnects over AI interconnect. [8] b) Explain the device isolation in details. [9] Explain basic properties of Silicon Wafer. **Q5**) a) [4] Explain steps in active region formation. b) [4] Explain Chemical vapor oxidation technique. c) [8] OR Write a short note on *Q6*) a) [8] Czochrlski and Float-Zone Crystal Growth Methods i) ii) Mask engineering

	SECTION-II	
Q7) a)	Explain merits and demerits of FPGA over ASIC.	[8]
b)	Compare data flow, behavioral and structural modeling styles.	[9]
	OR	
Q8) a)	Explain the following terms with examples.	
	i) Concurrent statements	
	ii) Variable	
	iii) Entity	
b)	Write VHDL Code for	[8]
	i) 8:1 Multiplexer.	
	ii) D-Flip flop	
Q9) a)	Explain the PAL and PLA in details.	[8]
b)	Explain static and dynamic circuit design styles.	[8]
	OR	
Q10) a)	Explain static and dynamic behavior of CMOS devices and Circuits.[8]	
b)	Explain different digital design levels.	[8]
Q11) a)	Explain the metastability in details.	[5]
b)	Explain software aspects of digital design.	[8]
c)	Discuss logic levels and noise margins with respect to CMOS circu	iits.[4]
	OR	
Q12) a)	Draw a neat diagram and explain briefly 6-T SRAM.	[8]
b)	For Combinational Logic design explains the following design metro	rics.[9]
	i) Power Consumption	

[8]

b) Explain photolithography process in detail.



Propagation Delay

Noise margin

ii) iii)